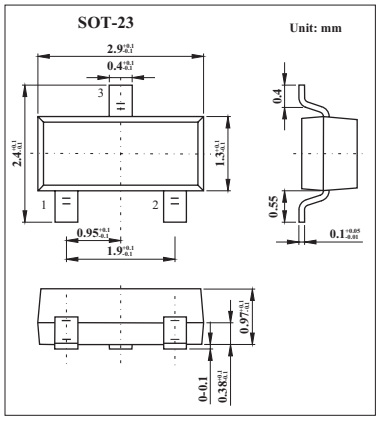
Schottky barrier (double) diodes

BAT754 series



Features

- Ultra high switching speed
- Guard ring protected
- Small plastic SMD package
- Low diode capacitance.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Continuous reverse voltage	V_R			30	V
Continuous forward current	I_F			200	mA
Repetitive peak forward current	I_{FRM}	tp < 1 s;δ < 0.5		300	mA
Non-repetitive peak forward current	I_{FSM}	tp = 8.3 ms half sinewave;JEDEC method		600	mA
Storage temperature	T_{stg}		-65	+150	℃
Junction temperature	T_j			125	℃
Operating ambient temperature	T_{amb}		-65	+125	℃

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Max	Unit
Forward voltage	V_F	I_F = 0.1 mA		200	mV
		I_F = 1 mA		260	mV
		I_F = 10 mA		340	mV
		I_F = 30 mA		420	mV
		I_F = 100 mA	600		mV
Reverse current	I_R	V_R = 25 V; Note 1		2	μA
Diode capacitance	C_d	f = 1 MHz; V_R = 1 V		10	pF

Note

1. Pulse test: t_p < 300 μs; δ ≤ 0.02.

Marking

Type	BAT754	BAT754A	BAT754C	BAT754S
Marking	2K	2L	2M	2N